Phonon-assisted optical absorption with EPW

Tutorial Thu. June 15

Hands-on session

Exercise

Before you start, please copy the tutorial tarball to your own scratch directory:

```
$ cp /work2/06868/giustino/EP-SCHOOL/Thu.4.Kioupakis.tar $SCRATCH
```

In this example we are going to calculate the phonon-assisted optical absorption spectrum of silicon. Extract the tarball Thu.4.Kioupakis.tar:

```
$ tar -xvf Thu.4.Kioupakis.tar
```

You can find all inputs we will use in this tutorial as well as some output files for verification purposes in the results folder. For a complete list of inputs please follow the link:

https://epwdoc.gitlab.io/source/doc/Inputs.html

You are advised to prepare the following queue submission script:

```
#!/bin/bash
#SBATCH --nodes=1
#SBATCH --ntasks-per-node=56
#SBATCH --account=EPSchool2022
#SBATCH --partition=small
#SBATCH --reservation=EPSchoolDay4
#SBATCH -t 01:00:00
PATHQE=/work2/06868/giustino/EP-SCHOOL/q-e/bin # this is the path to q-e
cd $PWD
```

Note: The path to the executables are set in the submission script. If you are using your own computer, remember to change the line to:

\$ export PATHQE='PATH-TO-QE/q-e/bin'

▶ Make a self-consistent calculation for Si.

```
&control
                   = 'scf'
  calculation
                   = 'si'
  prefix
                   = 'from_scratch'
  restart mode
                   = './'
  pseudo_dir
  outdir
                   = './'
1
&system
                   = 2
  ibrav
                   = 10.262
   celldm(1)
                   = 2
   nat
                   = 1
  ntyp
```

scf.in

```
ecutwfc
                    = 20
 1
&electrons
    diagonalization = 'david'
    mixing_beta
                    = 0.7
                    = 1.0d-13
    conv_thr
ATOMIC_SPECIES
 Si 28.0855 Si_r.upf
ATOMIC_POSITIONS alat
 Si 0.00 0.00 0.00
      0.25 0.25 0.25
 Si
K_POINTS automatic
12 \ 12 \ 12 \ 0 \ 0 \ 0
```

Note: The k-point grid needs to be fairly dense in order to get converged dielectric function and Born effective charge during the following phonon calculation.

```
$ ibrun -np 4 $PATHQE/pw.x < scf.in > scf.out
```

 \blacktriangleright Compute the vibrational properties of Si on a coarse 3x3x3 q-point grid.

```
$ ibrun -np 56 $PATHQE/ph.x -nk 28 < ph.in > ph.out &
```

The calculation should take about 1 min on 56 cores. During the run, notice the IBZ q-point grid (You can look at the output file or simply use the following command grep -6 Dynamical ph.out | tail -7):

```
Dynamical matrices for (3, 3, 3) uniform grid of q-points
( 4 q-points):
 Ν
           xq(1)
                         xq(2)
                                       xq(3)
     0.00000000
                                 0.00000000
  1
                   0.00000000
  2 -0.333333333
                   0.333333333
                                -0.333333333
  3
     0.000000000
                   0.666666667
                                 0.00000000
     0.666666667 -0.00000000
  4
                                 0.666666667
```

as well as the dielectric function and Born effective charge tensor (You can look at the otput file or simply use the following command grep -15 'Dielectric constant in' ph.out | tail -17):

Dielectric constant in cartesian axis

(12.982914533	0.00000000	0.000000000)
(0.00000000	12.982914533	-0.000000000)
(-0.00000000	-0.00000000	12.982914533)

Effective charges (d Force / dE) in cartesian axis

	atom	1 Si		
Ex	(-0.00778	0.00000	0.00000)
Ey	(0.00000	-0.00778	-0.00000)
Ez	(0.00000	-0.00000	-0.00778)
	atom	2 Si		
Ex	(-0.00778	-0.00000	-0.00000)
Ey	(-0.00000	-0.00778	-0.00000)
Ez	(0.00000	-0.00000	-0.00778)

The experimental dielectric constant of silicon is about 11.9 so that we overestimate it a bit. A smaller value can be obtained with larger k-point grids but DFT will always overestimate experiment. Since Si is a non polar material, the Born effective charges should be 0. Indeed, one can see that we are close to zero. In a converged calculation you may want to get an even smaller value.

► Like for the previous exercises, run the python post-processing to create the save folder (No job submission needed, can be ran simply on the login node.)

\$ python3 \$PATHQE/../EPW/bin/pp.py

▶ Do a non self-consistent calculation on a homogeneous 6x6x6 **positively defined between 0 and** 1 **k**-point grid.

```
&control
                                                                                                nscf.in
   calculation
                   = 'nscf'
   prefix
                  = 'si'
                  = 'from_scratch'
   restart_mode
   pseudo_dir
                   = './'
                   = './'
   outdir
 1
&system
   ibrav
                   = 2
   celldm(1)
                   = 10.262
   nat
                   = 2
   ntyp
                   = 1
   ecutwfc
                   = 20
                   = 12
   nbnd
 1
 &electrons
   diagonalization = 'david'
   mixing_beta = 0.7
   conv_thr
                   = 1.0d-10
 1
ATOMIC_SPECIES
 Si 28.0855 Si_r.upf
ATOMIC_POSITIONS alat
 Si 0.00 0.00 0.00
 Si
      0.25 0.25 0.25
K_POINTS crystal
216
 0.00000000 0.0000000 0.00000000 4.629630e-03
 0.00000000 0.0000000 0.16666667 4.629630e-03
. . .
```

\$ ibrun -np 4 \$PATHQE/pw.x -npool 4 < nscf.in > nscf.out

▶ Perform an EPW calculation to interpolate the electron-phonon matrix element from a coarse $6\times6\times6$ k and $3\times3\times3$ q-point grids to real space and then interpolate the electronic and phononic bandstructure along the $L - \Gamma - X$ high symmetry line.

___ epw1.in &inputepw prefix = 'si' = './' outdir elph = .true. epbwrite = .true. epbread = .false. epwwrite = .true. epwread = .false etf_mem = 1 nbndsub = 8

```
eig_read. = .true.
           = 'crystal'
asr tvp
use_ws.
           = .true.
wannierize = .true.
num_iter
          = 1500
           = 2
iprint
dis_win_max = 18
dis_froz_max= 9
proj(1) = 'Si : sp3'
wdata(1) = 'bands_plot = .true.'
wdata(2) = 'begin kpoint_path'
wdata(3) = 'L 0.50 0.00 0.00 G 0.00 0.00 '
wdata(4) = 'G 0.00 0.00 0.00 X 0.50 0.50 0.00'
wdata(5) = 'end kpoint_path'
wdata(6) = 'bands_plot_format = gnuplot'
wdata(7) = 'guiding_centres = .true.'
wdata(8) = 'dis_num_iter
                           = 500'
wdata(9) = 'num_print_cycles = 10'
wdata(10) = 'dis_mix_ratio = 1.0'
wdata(11) = 'use_ws_distance = T'
elecselfen = .false.
phonselfen = .false.
a2f
           = .false.
fsthick
           = 1.2 ! eV
           = 1 ! K
temps
degaussw = 0.005 ! eV
dvscf_dir = './save'
band_plot = .true.
           = './LGX.txt'
filkf
           = './LGX.txt'
filqf
           = 6
nk1
nk2
           = 6
nk3
            = 6
           = 3
nq1
nq2
           = 3
nq3
            = 3
```

\$ ibrun -np 56 \$PATHQE/epw.x -npool 56 < epw1.in > epw1.out

The calculation should take about 1 min. In the output, notice the additional information related to the crystal ASR. At the end of the calculation, because of the keyword band_plot = .true., the code will produce band.eig and phband.freq files that contains the electronic and phononic bandstructure along a path given by filkf and filqf. Note that the tag eig_read = .true. asks the code to read in an external set of eigenvalues (see si.eig) that needs to be on the same set of k-points grid and number of bands as the nscf calculation. Here a set of GW eigenvalues calculated with BerkeleyGW are provided.

Note: An option exists to use QE generated interatomic forces in EPW with setting lifc = .true.. This is not recommended, and instead, the combination of lifc = .false.(default) and use_ws = .true. to ensure construction of the correct Wigner-Seitz cell is always recommended for consistency.

If you want to convert the band.eig and phband.freq files into a format readable by gnuplot, you can use the plotband.x tool by doing: (No job submission needed, can be ran simply on the login node.)

\$ \$PATHQE/plotband.x

1

to launch a command line interface for the file generation. Note that the second prompt will define the y-axis bounds. You should check that both bandstructure looks reasonable.

► Do a restart calculation (restarting from the si.epmatwp file) and compute the phonon-assisted absorption spectrum of silicon in the visible range.

The phonon-assisted optical absorption formalism is presented in J. Noffsinger *et al.*, *Phys. Rev Lett.* **108**, 167402 (2012). The code calculates the imaginary part of the dielectric function due to phonon-assisted optical transitions in the spectral region between the indirect and direct band gaps:

$$\varepsilon_2(\omega) = \frac{8\pi^2 e^2}{\Omega \omega^2} \frac{1}{N_{\mathbf{k}} N_{\mathbf{q}}} \sum_{\nu i j \mathbf{k} \mathbf{q}} |\mathbf{e} \cdot (\mathbf{S}_1 + \mathbf{S}_2)|^2$$
(1)

$$\times P\delta(\epsilon_{j,\mathbf{k}+\mathbf{q}} - \epsilon_{i,\mathbf{k}} - \hbar\omega \pm \hbar\omega_{\nu\mathbf{q}}) \tag{2}$$

where $\hbar\omega$ and e are the energy and polarization of the photon. The generalized optical matrix elements, S_1 and S_2 , are given by

$$\mathbf{S}_{1}(\mathbf{k},\mathbf{q}) = \sum_{m} \frac{\mathbf{v}_{im}(\mathbf{k})g_{mj,\nu}(\mathbf{k},\mathbf{q})}{\epsilon_{m\mathbf{k}} - \epsilon_{i\mathbf{k}} - \hbar\omega + i\Gamma_{m,\mathbf{k}}},\tag{3}$$

$$\mathbf{S}_{2}(\mathbf{k},\mathbf{q}) = \sum_{m} \frac{g_{im,\nu}(\mathbf{k},\mathbf{q})\mathbf{v}_{mj}(\mathbf{k}+\mathbf{q})}{\epsilon_{m,\mathbf{k}+\mathbf{q}} - \epsilon_{i\mathbf{k}} \pm \hbar\omega_{\nu\mathbf{q}} + i\Gamma_{m,\mathbf{k}+\mathbf{q}}},\tag{4}$$

and correspond to the two possible paths of the indirect absorption process labelled (1) and (2) in the figure below:



They are determined in terms of the velocity (\mathbf{v}) and electron-phonon coupling (g) matrix elements, as well as the real $(\epsilon_{n\mathbf{k}})$ and imaginary $(\Gamma_{n\mathbf{k}})$ parts of the quasiparticle self-energies. The factor P accounts for the carrier and phonon statistics,

$$P_a = n_{\nu \mathbf{q}} \times f_{i,\mathbf{k}} \times (1 - f_{j,\mathbf{k}+\mathbf{q}}) - (n_{\nu \mathbf{q}} + 1) \times (1 - f_{i,\mathbf{k}}) \times f_{j,\mathbf{k}+\mathbf{q}}$$
(5)

$$P_e = (n_{\nu \mathbf{q}} + 1) \times f_{i,\mathbf{k}} \times (1 - f_{j,\mathbf{k}+\mathbf{q}}) - n_{\nu \mathbf{q}} \times (1 - f_{i,\mathbf{k}}) \times f_{j,\mathbf{k}+\mathbf{q}}$$
(6)

The P factors can be obtained by considering energy conservation of the absorption/emission process.

The input file is as follows:

___ &inputepw prefix = 'si' = './' outdir elph = .true. epbwrite = .false. = .false. epbread epwwrite = .false. = .true. = 1 epwread etf_mem ! band_plot = .true. mp_mesh_k = .true. lindabs = .true. efermi_read = .true. $fermi_energy = 5.57$ eig_read = .true. omegamin = 0.05 omegamax = 3.0omegastep = 0.05elecselfen = .false. phonselfen = .false. = .false. a2f fsthick = 4.0 ! eV temps = 300 ! K degaussw = 0.05 ! eV dvscf_dir = './save' = 12 nkf1 nkf2 = 12 = 12 nkf3 nqf1 = 6 = 6 nqf2 nqf3 = 6 = 6 nk1 nk2 = 6 nk3 = 6 = 3 nq1 nq2 = 3 = 3 nq3 = 8 nbndsub use_ws = .true. asr_typ = 'crystal' wannierize = .false. 1

Notes:

• epwread allows for the restart from the si.epmatwp file.

epw2.in

- lindabs enables phonon-assisted optical absorption calculations.
- mp_mesh_k use only the irr. wedge for the fine electronic mesh. This reduces the computational cost significantly.
- omegamin, omegamax, omegastep are the minimum, maximum, and spacing of the photon energies for which we calculate the absorption coefficient.
- fermi_energy = 5.57 sets the Fermi energy for silicon (insulator) in the middle of the gap, and fsthick = 4.0 limits the absorption calculation to states within an energy window around the Fermi level (set to be larger than the maximum photon energy we want the absorption spectra for plus the maximum phonon energy of the material).
- The code calculates the spectra with nine different broadening parameter values (Γ in the S-parameters, where $\Gamma = 0.001, 0.002, 0.005, 0.01, 0.02, 0.05, 0.1, 0.2, 0.5 \text{ eV}$). Note that within the indirect region of the spectra, the choice of the broadening of the denominator does not affect the spectra significantly.
- \$ ibrun -np 56 \$PATHQE/epw.x -npool 56 < epw2.in > epw2.out

The run should take less than 1 min. You can find the directionally-averaged imaginary part of the phonon-assisted dielectric function for the different broadenings in epsilon2_indabs_300.0K.dat (Gaussian broadening for delta function) or epsilon2_indabs_lorenz300.0K.dat (Lorentzian broadening for delta function).¹ The first column is photon energy, while the other columns are the corresponding $\varepsilon_2(\omega)$ for different Γ s. The result should look like this (for the first Γ with Gaussian broadening for the delta function):



The fine k and q point grids need to be denser for production calculations. At convergence you should get a result similar to Fig. 3 of J. Noffsinger *et al.*, *Phys. Rev Lett.* **108**, 167402 (2012). Note that the relationship between Im $\varepsilon(\omega)$ and the absorption coefficient is $\alpha(\omega) = \frac{\omega}{cn_r(\omega)} \text{Im } \varepsilon(\omega)$. The paper assumes a constant refractive index of $n_r = 3.4$.

 $^{^{1}}$ Note that direct absorption within the independent particle approximation is also calcualted, see epsilon2_dirabs_300.0K.dat and epsilon2_dirabs_lorenz300.0K.dat. Careful convergence with respect to k-grid is important.



▶ Increase the fine grids to improve convergence.

You can also perform calculations to study the onset of phonon-assisted absorption and see the separate contributions from the phonon-absorption and the phonon-emission terms. These calculations need a small broadening parameter on the order of 10 meV (smaller than the phonon frequency) to distinguish the different onsets of the phonon-absorption and phonon-emission terms as well as fine k and q grids on the order of $40 \times 40 \times 40$. You can accelerate these calculations by selecting a narrow omegamin and omegamax range near the indirect absorption onset and adjusting the fsthick window accordingly. The converged result is similar to the spectra below from J. Noffsinger *et al.*, *Phys. Rev. Lett.* **108**, 167402 (2012):



► Optional: phonon-assisted free-carrier absorption (FCA)

In addition to the phonon-assisted optical absorption, you can add the combination of tags carrier and ncarrier to specify the carrier density in n-type (positive ncarrier) or p-type (negative ncarrier) semiconductors to study phonon-assisted free-carrier absorption. The input for such a calculation is provided in epw3.in.

	epw3.ir
&inputepw	
omegamin = 0.05	
omegamax = 3.0	
omegastep = 0.05	
carrier = .true.	
ncarrier = 1e19	
nkf1 = 16	
nkf2 = 16	
nkf3 = 16	
nqf1 = 16	
nqf2 = 16	
nqf3 = 16	
/	

Note that the k- and q-points grid are finer in the input for this optional calculation. Since freecarrier absorption happens close to the conduction band minimum or valence band maximum, a much denser grid is necessary to obtain converged result. In practice, one can typically use a smaller value of fsthick to reduce the computational cost due to that free-carrier absorption is dominant only in sub-gap region where photon energy is relatively small compared to cross-gap indirect absorption.

Take a look at the output epsilon2_indabs_300.0K.dat, you will notice the $\varepsilon_2(\omega)$ now contains sub-gap contributions that results from free-carrier absorption. You may also notice that the spectrum now has a strong dependence on the broadening Γ in Eq.(3) and Eq.(4), which is due to the divergence of the denominator. This divergence is present when direct transition (in this case, interconduction bands) is possible, and is a limitation of the second-order perturbation theory itself. It can be reduced by numerical approaches to cancel the diverging term, see e.g. Brown *et al.*, ACS Nano, **10.1**, 957-966 (2016).

More details about free-carrier absorption can be found at: https://arxiv.org/abs/2205.02768